

HVM121WK

Silicon Epitaxial Planar PIN Diode for High Frequency Attenuator

HITACHI

Preliminary
Rev. 3
Jun. 1993

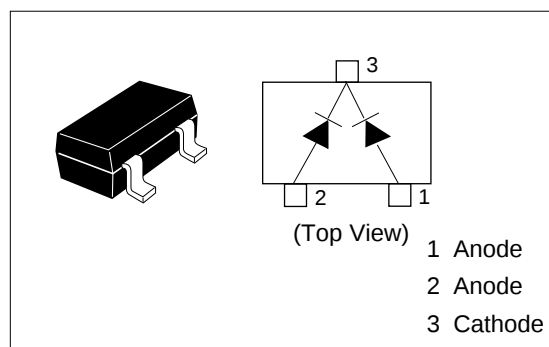
Features

- Low capacitance. ($C = 0.7\text{pF}$ max)
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HVM121WK	H 4	MPAK

Pin Arrangement



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

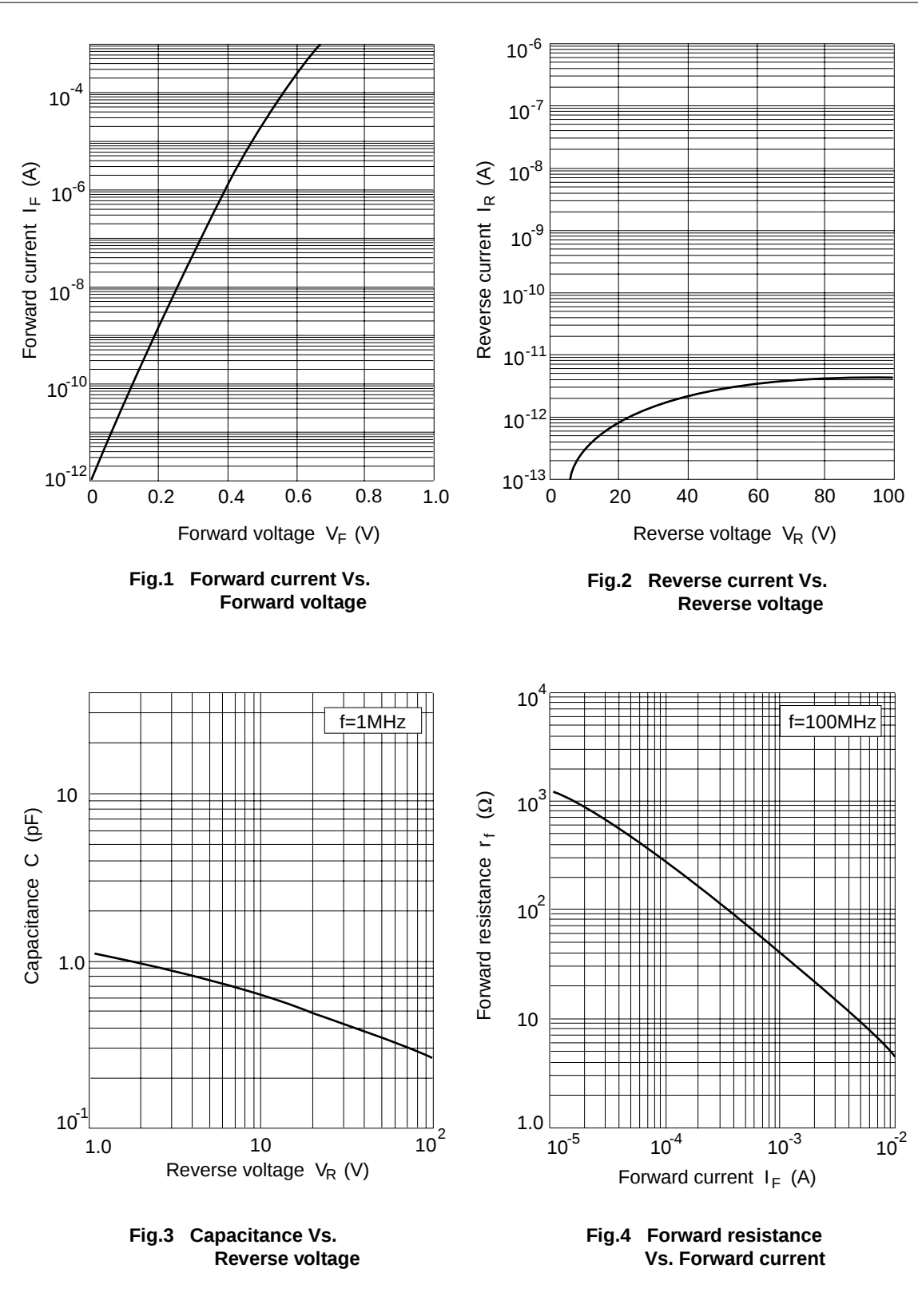
Item	Symbol	Value	Unit
Reverse voltage	V_R	100	V
Forward current	I_F	50	mA
Power dissipation	P_d^*	100	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

* Per one device

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.1	V	$I_F = 50\text{ mA}$
Reverse current	I_R	—	—	100	nA	$V_R = 30\text{ V}$
Capacitance	C	—	—	0.7	pF	$V_R = 50\text{ V}$, $f = 1\text{ MHz}$
Forward resistance	r_{f1}	1.0	—	—	$\text{k}\Omega$	$I_F = 10\text{ }\mu\text{A}$, $f = 100\text{ MHz}$
	r_{f2}	—	—	10	Ω	$I_F = 10\text{ mA}$, $f = 100\text{ MHz}$

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Package Dimensions

Unit: mm

